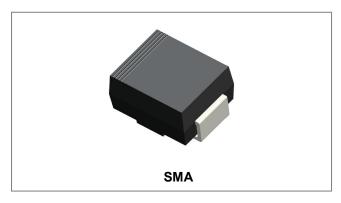






# **SK315A SCHOTTKY RECTIFIER**



## **Features**

- Small foot print, surface mountable
- Very low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term
- reliability
- Green products in compliance the ROHS directive
- This is a Pb Free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

# **Circuit Diagram**



## **Applications**

- · Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ \end{array}$	-	150	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @T <sub>L</sub> =100°C, rectangular wave form	3	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T <sub>c</sub> = 25 °C	80	А

## **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 3A, Pulse, T <sub>J</sub> = 25 °C	0.79	0.89	V
	V <sub>F1</sub>	@ 3A, Pulse, T <sub>J</sub> = 125 °C	0.65	0.79	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_{R_1} T_J = 25 ^{\circ}\text{C}$	0.003	1.0	mA
	I <sub>R2</sub>	$@V_R = \text{rated } V_{R_1} T_J = 125  ^{\circ}\text{C}$	0.2	7.0	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25  ^{\circ}C, f_{SIG} = 1MHz$	70	100	pF
Series Inductance	L <sub>S</sub>	Measured lead to lead 5 mm from 8.0		-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

<sup>•</sup> China - Germany - Korea - Singapore - United States •

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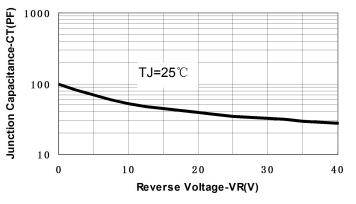




# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Lead	$R_{ heta JL}$	DC operation	20	°C/W
Typical Thermal Resistance Junction to Ambient	$R_{ heta JA}$	DC operation	77	°C/W
Approximate Weight	wt	-	0.06	g

# **Ratings and Characteristics Curves**



TJ=25°C

0. 01

0. 01

TJ=125°C

0. 0001

0 30 60 90 120 150

Reverse Voltage-VR(V)

Fig.1-Typical Junction Capacitance

**Fig.2-Typical Reverse Characteristics** 

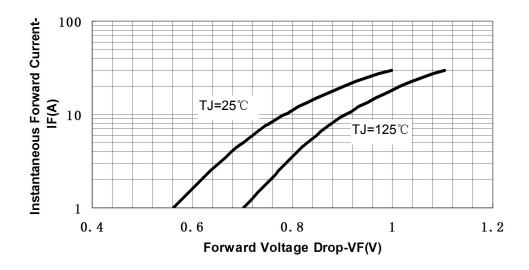


Fig.3-Typical Instantaneous Forward Voltage Characteristics

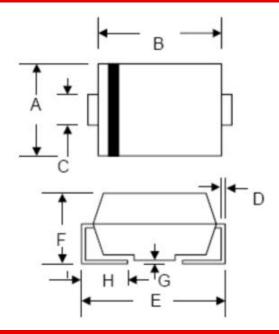
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## **Mechanical Dimensions SMA**



SYMBOL	Millimeters		Inches		
STIVIBUL	Min.	Max.	Min.	Max.	
Α	2.40	2.84	0.094	0.112	
В	3.99	4.75	0.157	0.187	
С	1.05	1.70	0.041	0.067	
D	0.15	0.51	0.006	0.020	
Е	4.80	5.66	0.189	0.223	
F	1.90	2.95	0.075	0.116	
G	0.05	0.203	0.002	0.008	
Н	0.76	1.52	0.030	0.600	

# **Ordering Information**

Device	Package	Shipping
SK315A	SMA (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**

A315 XXXXX Where XXXXX is YYWWL

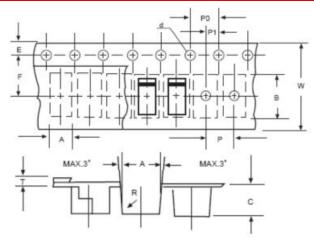
= Package type = Forward Current (3A) = Reverse Voltage (150V)

YY = Year WW = Week L = Lot Number

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**Cautions:** Molding resin Epoxy resin UL:94V-0

# **Carrier Tape & Reel Specification SMA**



SYMBOL	Millimeters		
	Min.	Max.	
Α	2.97	3.17	
В	5.70	5.90	
С	2.32	2.52	
d	1.40	1.60	
E	1.40	1.60	
F	5.60	5.70	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
Т	0.25	0.35	
W	11.80	12.20	

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